

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): An etching substrate material comprising a metal substrate material which is to be provided thereon a pattern by coating a photosensitive resin layer formed thereon, and exposing the photosensitive resin layer to light to form a resist pattern, followed by etching, characterized in that said etching substrate material has a center line-average surface roughness Ra of ~~up to~~ less than $0.10\ \mu\text{m}$ and a maximum surface roughness Rmax of ~~up to~~ less than $1.0\ \mu\text{m}$.

2. (original): The etching substrate material according to claim 1, characterized in that a surface roughness of said metal substrate material has been regulated by at least one process selected from the group consisting of rolling, chemical polishing, physical polishing, and electrolytic polishing.

3. (currently amended): The etching substrate material according to claim ~~4~~ 5, characterized in that said metal substrate material is a substrate material for a shadow mask, an aperture grill or a lead frame.

4. (currently amended): The etching substrate material according to claim ~~2~~ 5, characterized in that said metal substrate material is a substrate material for a shadow mask, an aperture grill or a lead frame.

5. (new): An etching substrate material comprising a metal substrate material which is to be provided thereon a pattern by coating a photosensitive resin layer formed thereon, and exposing the photosensitive resin layer to light to form a resist pattern, followed by etching, characterized in that said etching substrate material has a center line-average surface roughness Ra of less than $0.10\ \mu\text{m}$ and a maximum surface roughness Rmax of less than $1.0\ \mu\text{m}$,

characterized in that a surface roughness of said metal substrate material has been regulated by at least one process selected from the group consisting of rolling, chemical polishing, physical polishing, and electrolytic polishing.